## 1SS181

## SILICON EPITAXIAL PLANAR DIODE

## Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance


## Applications



Marking Code: A1
SOT-23 Plastic Package

- Ultra high speed switching application

Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Maximum Peak Reverse Voltage | $\mathrm{V}_{\mathrm{RM}}$ | 85 | V |
| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 80 | V |
| Average Forward Current | $\mathrm{I}_{\mathrm{O}}$ | 100 | mA |
| Maximum Peak Forward Current | $\mathrm{I}_{\mathrm{FM}}$ | 300 | mA |
| Surge Current (10 ms) | $\mathrm{I}_{\mathrm{FSM}}$ | 2 | A |
| Power Dissipation | $\mathrm{P}_{\text {tot }}$ | 150 | mW |
| Junction Temperature | $\mathrm{T}_{\mathrm{j}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\mathrm{s}}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Characteristics at $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Max. | Unit |
| :--- | :---: | :---: | :---: |
| Forward Voltage <br> at $\mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA}$ | $\mathrm{~V}_{\mathrm{F}}$ | 1.2 | V |
| Reverse Current <br> at $\mathrm{V}_{\mathrm{R}}=30 \mathrm{~V}$ <br> at $\mathrm{V}_{\mathrm{R}}=80 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{R}}$ | 0.1 | $\mu \mathrm{~A}$ |
| Total Capacitance <br> at $\mathrm{V}_{\mathrm{R}}=0, \mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{C}_{\mathrm{T}}$ | 0.5 | pF |
| Reverse Recovery Time <br> at $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}$ | $\mathrm{t}_{\mathrm{rr}}$ | 4 | ns |



Fig. 1 Reverse recovery time ( $\mathrm{t}_{\mathrm{r}}$ ) test circuit

INPUT WAVEFORM
$0.01 \mu \mathrm{~F}$ DUT
$\left.6 \mathrm{~V}\right|_{\text {- }} ^{0}$
PULSE GENERATOR
$\left(\mathrm{R}_{\mathrm{OUT}}=50 \Omega\right)$

## OUTPUT WAVEFORM



